# **Small Signal MOSFET**

# 20 V, 220 mA, Dual N-Channel, 1.0 mm x 1.0 mm SOT-963 Package

#### **Features**

- Dual N-Channel MOSFET
- Offers a Low R<sub>DS(ON)</sub> Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics
- This is a Pb-Free Device

# **Applications**

- General Purpose Interfacing Switch
- Optimized for Power Management in Ultra Portable Equipment
- Analog Switch

# MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise specified)

| Para  | Symbol           | Value                 | Unit              |        |    |  |
|---|------------------|-----------------------|-------------------|--------|----|--|
| Drain-to-Source Voltage   |                  |                       | V <sub>DSS</sub>  | 20     | V  |  |
| Gate-to-Source Voltage  |                  |                       | V <sub>GS</sub>   | ±8     | V  |  |
| Continuous Drain  | Steady           | $T_A = 25^{\circ}C$   |                   | 220    | mA |  |
| Current (Note 1)  | State            | $T_A = 85^{\circ}C$   | $I_{D}$           | 160    |    |  |
|   | t ≤ 5 s          | $T_A = 25^{\circ}C$   |                   | 280    |    |  |
| Power Dissipation   | Steady<br>State  | T <sub>A</sub> = 25°C |                   | 125    |    |  |
| (Note 1)  |                  |                       | $P_{D}$           |        | mW |  |
|   | t ≤ 5 s          |                       |                   | 200    |    |  |
| Pulsed Drain Current $t_p = 10 \mu s$                             |                  |                       | I <sub>DM</sub>   | 800    | mA |  |
| Operating Junction and Storage Temperature                        |                  |                       | _T <sub>J</sub> , | -55 to | °C |  |
|   | T <sub>STG</sub> | 150                   |                   |        |    |  |
| Source Current (Body Diode) (Note 2)                              |                  |                       | IS                | 200    | mA |  |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) |                  |                       | TL                | 260    | °C |  |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface–mounted on FR4 board using the minimum recommended pad size,

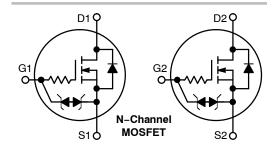
- 2. Pulse Test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%

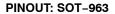


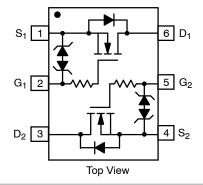
# ON Semiconductor®

## http://onsemi.com

| V <sub>(BR)DSS</sub> | R <sub>DS(ON)</sub> MAX | I <sub>D</sub> Max |
|----------------------|-------------------------|--------------------|
|                      | 1.5 Ω @ 4.5 V           |                    |
| 20 V                 | 2.0 Ω @ 2.5 V           | 0.22 A             |
|                      | 3.0 Ω @ 1.8 V           |                    |
|                      | 4.5 Ω @ 1.5 V           |                    |









SOT-963 CASE 527AD

3

**MARKING** DIAGRAM

= Specific Device Code

М = Date Code

= Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

## THERMAL RESISTANCE RATINGS

| Parameter                                   | Symbol        | Max  | Unit         |
|---|---------------|------|--------------|
| Junction-to-Ambient - Steady State (Note 3) | $R_{	hetaJA}$ | 1000 | °C/W         |
| Junction-to-Ambient - t = 5 s (Note 3)      | ' ч⊎JА        | 600  | O/ <b>VV</b> |

<sup>3.</sup> Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

# **ELECTRICAL CHARACTERISTICS** ( $T_J = 25$ °C unless otherwise specified)

| Parameter                                    | Symbol               | Test Condition  | on                    | Min | Тур  | Max  | Unit |
|--|----------------------|---|-----------------------|-----|------|------|------|
| OFF CHARACTERISTICS                          | •                    | •   |                       | •   |      |      |      |
| Drain-to-Source Breakdown Voltage            | V <sub>(BR)DSS</sub> | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$                               |                       | 20  |      |      | V    |
| Zero Gate Voltage Drain Current              |                      | ., .,,,   | T <sub>J</sub> = 25°C |     |      | 50   | nA   |
|  | I <sub>DSS</sub>     | $V_{GS} = 0 \text{ V}, V_{DS} = 5 \text{ V}$                                | T <sub>J</sub> = 85°C |     |      | 200  |      |
|  |                      | V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 16 V                               | T <sub>J</sub> = 25°C |     |      | 100  | nA   |
| Gate-to-Source Leakage Current               | I <sub>GSS</sub>     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±5.0 V                             |                       |     |      | ±100 | nA   |
| ON CHARACTERISTICS (Note 4)                  | •                    |   |                       |     |      |      |      |
| Gate Threshold Voltage                       | V <sub>GS(TH)</sub>  | $V_{GS} = V_{DS}$ , $I_D = 2$   | 250 μA                | 0.4 |      | 1.0  | V    |
| Drain-to-Source On Resistance                |                      | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 100 mA                            |                       |     | 0.75 | 1.5  |      |
|  |                      | V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 50 mA                             |                       |     | 1.0  | 2.0  | Ω    |
|  | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 20 mA                             |                       |     | 1.4  | 3.0  |      |
|  |                      | V <sub>GS</sub> = 1.5 V, I <sub>D</sub> = 10 mA                             |                       |     | 1.8  | 4.5  |      |
|  |                      | V <sub>GS</sub> = 1.2 V, I <sub>D</sub> = 1.0 mA                            |                       |     | 2.8  |      |      |
| Forward Transconductance                     | 9 <sub>FS</sub>      | V <sub>DS</sub> = 5.0 V, I <sub>D</sub> = 125 mA                            |                       |     | 0.48 |      | S    |
| Source-Drain Diode Voltage                   | V <sub>SD</sub>      | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 10 mA                               |                       |     | 0.6  | 1.0  | V    |
| CAPACITANCES                                 | •                    |   |                       |     |      |      |      |
| Input Capacitance                            | C <sub>ISS</sub>     |   |                       |     | 12.5 |      |      |
| Output Capacitance                           | C <sub>OSS</sub>     | f = 1.0 MHz, V <sub>GS</sub> = 0 V<br>V <sub>DS</sub> = 15 V                |                       |     | 3.6  |      | pF   |
| Reverse Transfer Capacitance                 | C <sub>RSS</sub>     |   |                       |     | 2.6  |      |      |
| SWITCHING CHARACTERISTICS, V <sub>GS</sub> = | 4.5 V (Note 4)       |   |                       | -   | -    |      |      |
| Turn-On Delay Time                           | t <sub>d(ON)</sub>   | $V_{GS}$ = 4.5 V, $V_{DD}$ = 10 V, $I_{D}$ = 200 mA, $R_{G}$ = 2.0 $\Omega$ |                       |     | 16.5 |      | - ns |
| Rise Time                                    | t <sub>r</sub>       |   |                       |     | 25.5 |      |      |
| Turn-Off Delay Time                          | t <sub>d(OFF)</sub>  |   |                       |     | 142  |      |      |
| Fall Time                                    | t <sub>f</sub>       |   |                       |     | 80   |      |      |

 $<sup>{\</sup>bf 4.} \ \ {\bf Switching\ characteristics\ are\ independent\ of\ operating\ junction\ temperatures.}$ 

## **ORDERING INFORMATION**

| Device        | Package              | Shipping <sup>†</sup> |  |  |
|---------------|----------------------|-----------------------|--|--|
| NTUD3170NZT5G | SOT-963<br>(Pb-Free) | 8000 / Tape & Reel    |  |  |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **TYPICAL CHARACTERISTICS**

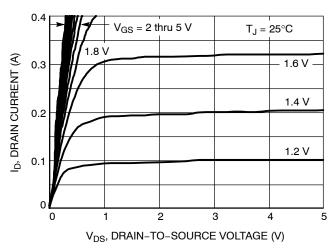
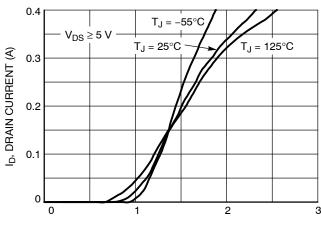


Figure 1. On-Region Characteristics



V<sub>GS</sub>, GATE-TO-SOURCE VOLTAGE (V)

Figure 2. Transfer Characteristics

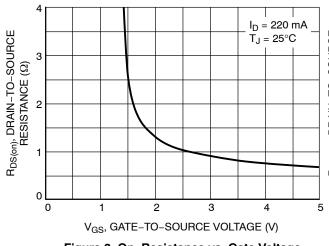


Figure 3. On-Resistance vs. Gate Voltage

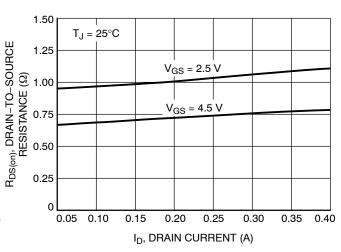


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

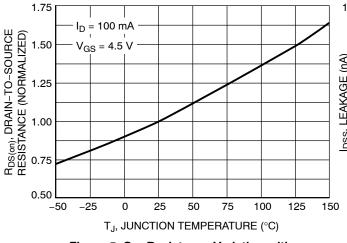


Figure 5. On–Resistance Variation with Temperature

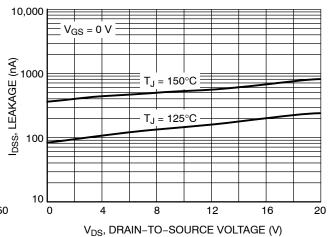
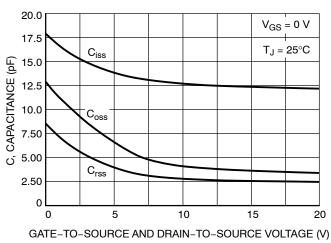
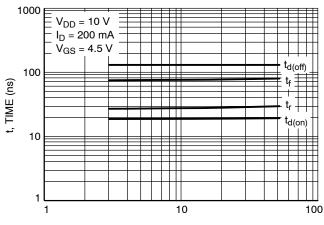


Figure 6. Drain-to-Source Leakage Current vs. Voltage

# **TYPICAL CHARACTERISTICS**





 $R_G$ , GATE RESISTANCE ( $\Omega$ )

Figure 7. Capacitance Variation

Figure 8. Resistive Switching Time Variation vs. Gate Resistance

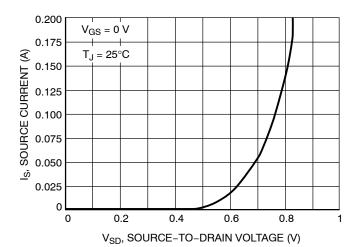
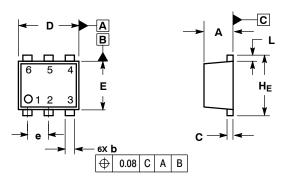


Figure 9. Diode Forward Voltage vs. Current

## PACKAGE DIMENSIONS

# SOT-963 CASE 527AD-01 ISSUE D

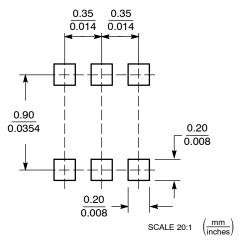


- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- T14-3M, 1962.

  CONTROLLING DIMENSION: MILLIMETERS
  MAXIMUM LEAD THICKNESS INCLUDES LEAD
  FINISH THICKNESS. MINIMUM LEAD THICKNESS
  IS THE MINIMUM THICKNESS OF BASE MATERIAL.

|     | MILLIMETERS |      |      | INCHES |          |       |
|-----|-------------|------|------|--------|----------|-------|
| DIM | MIN         | NOM  | MAX  | MIN    | NOM      | MAX   |
| Α   | 0.34        | 0.37 | 0.40 |        |          |       |
| b   | 0.10        | 0.15 | 0.20 | 0.004  | 0.006    | 0.008 |
| С   | 0.07        | 0.12 | 0.17 | 0.003  | 0.005    | 0.007 |
| D   | 0.95        | 1.00 | 1.05 | 0.037  | 0.039    | 0.041 |
| Е   | 0.75        | 0.80 | 0.85 | 0.03   | 0.032    | 0.034 |
| е   | 0.35 BSC    |      |      | (      | 0.014 BS | C     |
| L   | 0.05        | 0.10 | 0.15 | 0.002  | 0.004    | 0.006 |
| HE  | 0.95        | 1.00 | 1.05 | 0.037  | 0.039    | 0.041 |

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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